

VRRM	IF ( TC≤135℃)	QC
650V	9A	18nC

### Applications:

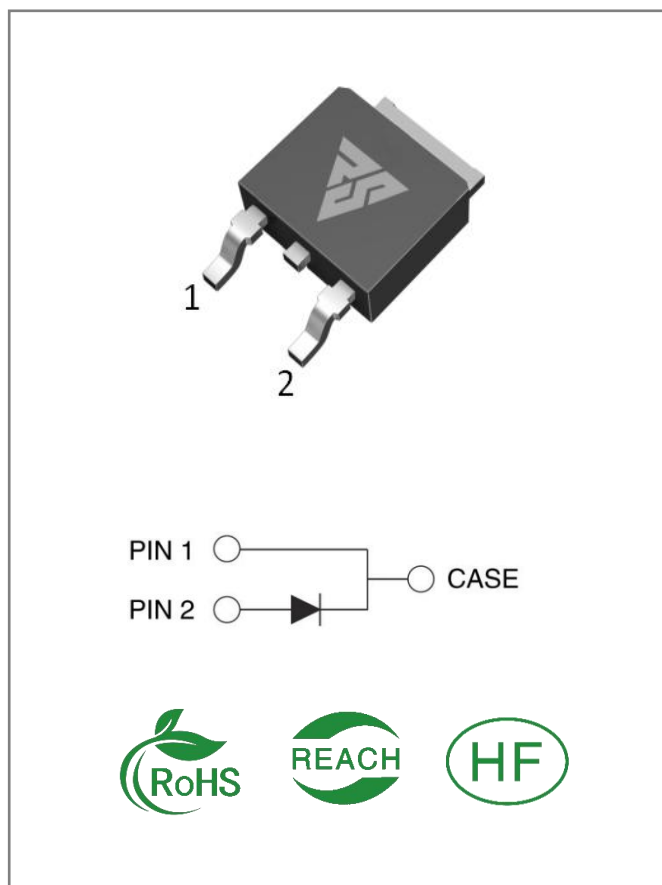
- Switch Mode Power Supplies
- Power Factor Correction
- Motor drive, PV Inverter, Wind Power Station

### Features:

- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Positive Temperature Coefficient on VF
- Temperature-independent Switching
- 175°C Operating Junction Temperature

### Benefits:

- Replace Bipolar with Unipolar Device
- Reduction of Heat Sink Size
- Parallel Devices Without Thermal Runaway
- Essentially No Switching Losses



### Ordering Information

Part Number	Package	Marking	Packing	Qty.
RSS06065D	TO-252	RSS06065D	Tape&reel	2500 PCS

**Maximum Ratings** (T<sub>J</sub>= 25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
VRRM	Repetitive Peak Reverse Voltage	650	V	TC = 25°C	
VRSM	Surge Peak Reverse Voltage	650	V	TC = 25°C	
VR	DC Blocking Voltage	650	V	TC = 25°C	
IF	Forward Current	20 9 6	A	TC ≤ 25°C TC ≤ 135°C TC ≤ 153°C	Fig.3
IFSM	Non-Repetitive Forward Surge Current	66 57	A	TC = 25°C, tp = 10ms, Half Sine Wave TC = 110°C, tp = 10ms, Half Sine Wave	
IFRM	Repetitive Peak Forward Surge Current	60	A	TC = 25°C, tp = 10ms, Half Sine Wave	
Ptot	Power Dissipation	87	W	TC = 25°C	Fig.4
TC	Maximum Case Temperature	153	°C		
TJ,TST G	Operating Junction and Storage Temperature	-55 to175	°C		

**Electrical Characteristics** (T<sub>J</sub>= 25°C unless otherwise specified)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
VF	Forward Voltage	1.34 1.67	1.5 -	V	IF = 6A, T <sub>J</sub> = 25°C IF = 6A, T <sub>J</sub> = 175°C	Fig.1
IR	Reverse Current	1.2 4.5	50 -	μA	VR = 650V, T <sub>J</sub> = 25°C VR = 650V, T <sub>J</sub> = 175°C	Fig.2
C	Total Capacitance	261 35 33	/	pF	VR = 1V, T <sub>J</sub> = 25°C, f = 1MHz VR = 200V, T <sub>J</sub> = 25°C, f = 1MHz VR = 400V, T <sub>J</sub> = 25°C, f = 1MHz	Fig.5
QC	Total Capacitive Charge	18	/	nC	VR = 400V,	Fig.6
Ec	Capacitance Stored Energy	2.9		uJ	VR = 400V,	Fig.7

**Thermal Characteristics** (T<sub>J</sub>= 25°C unless otherwise specified)

Symbol	Parameter	Typ.	Unit	Note
RθJC	Thermal Resistance from Junction to Case	1.73	°C/W	Fig.8

## Typical Feature Curve

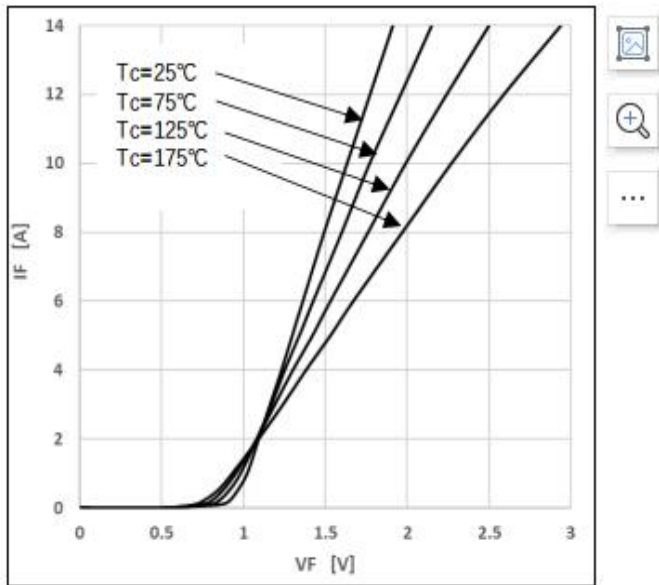


Figure 1 Forward Characteristics

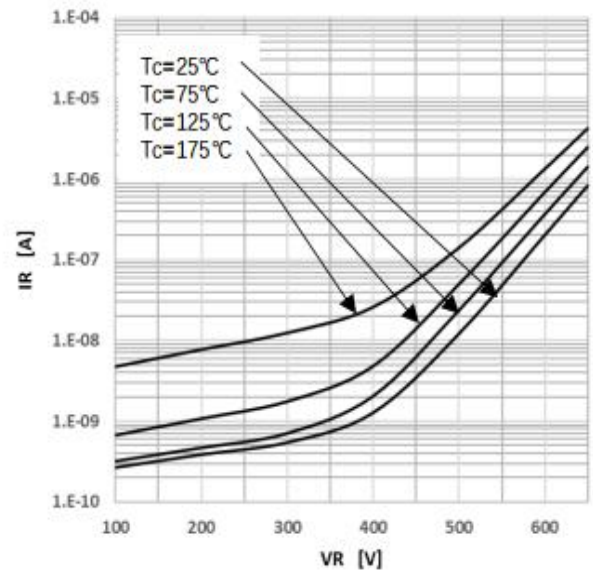


Figure 2 Reverse Characteristics

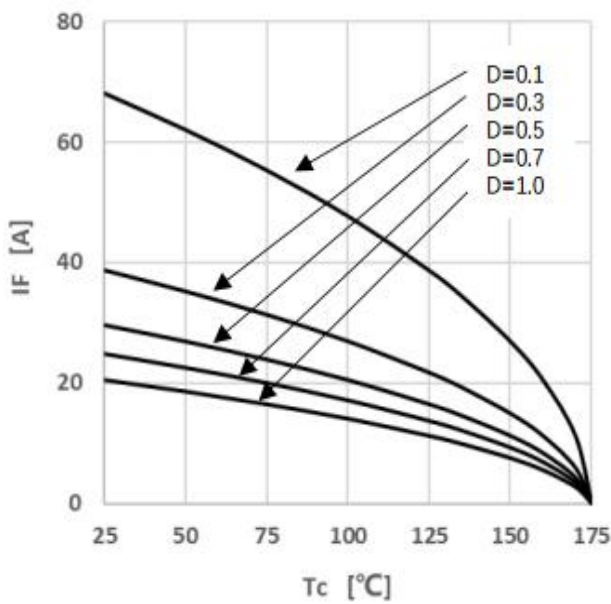


Figure 3 Peak Forward Current Derating

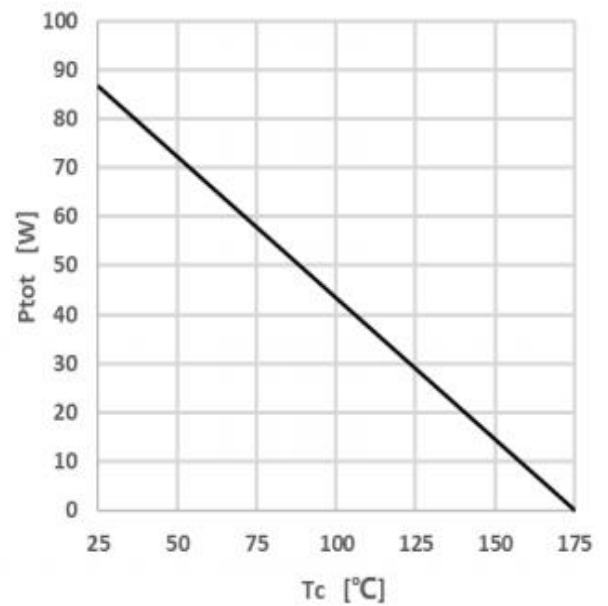


Figure 4 Power Dissipation

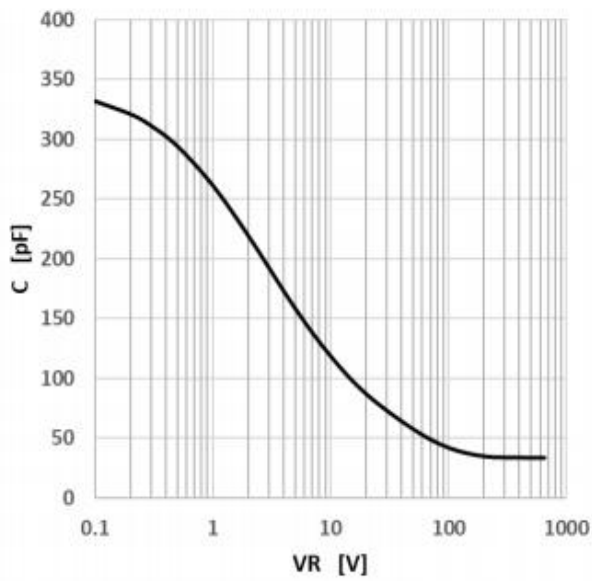


Figure 5 Capacitance vs. Reverse Voltage

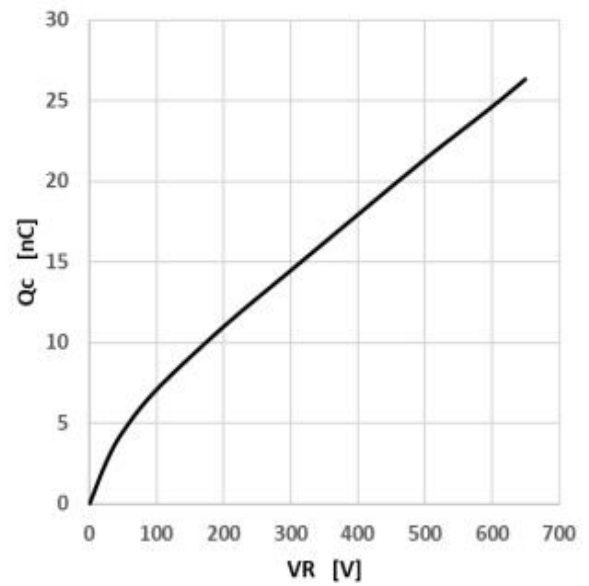


Figure 6 Capacitance Charge vs. Reverse Voltage

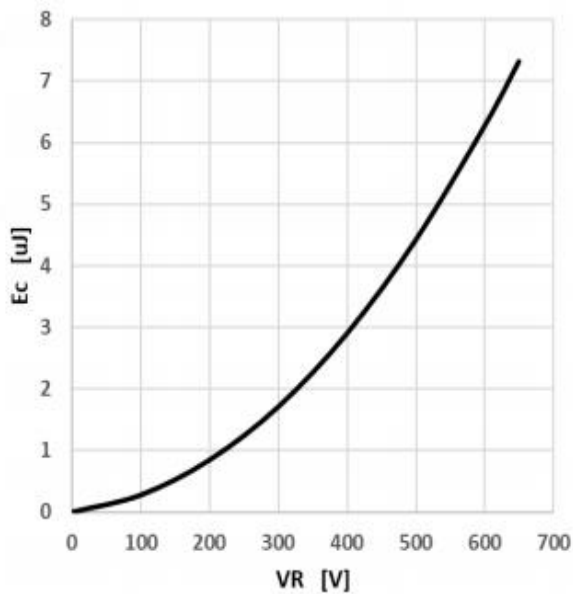


Figure 7 Capacitance Stored Energy

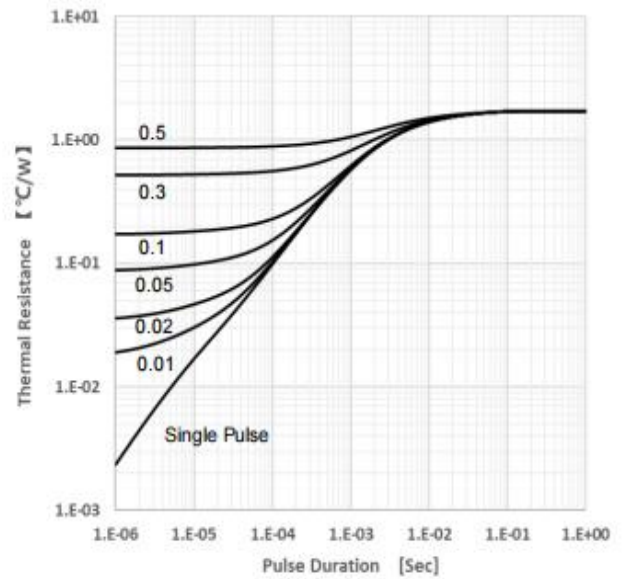
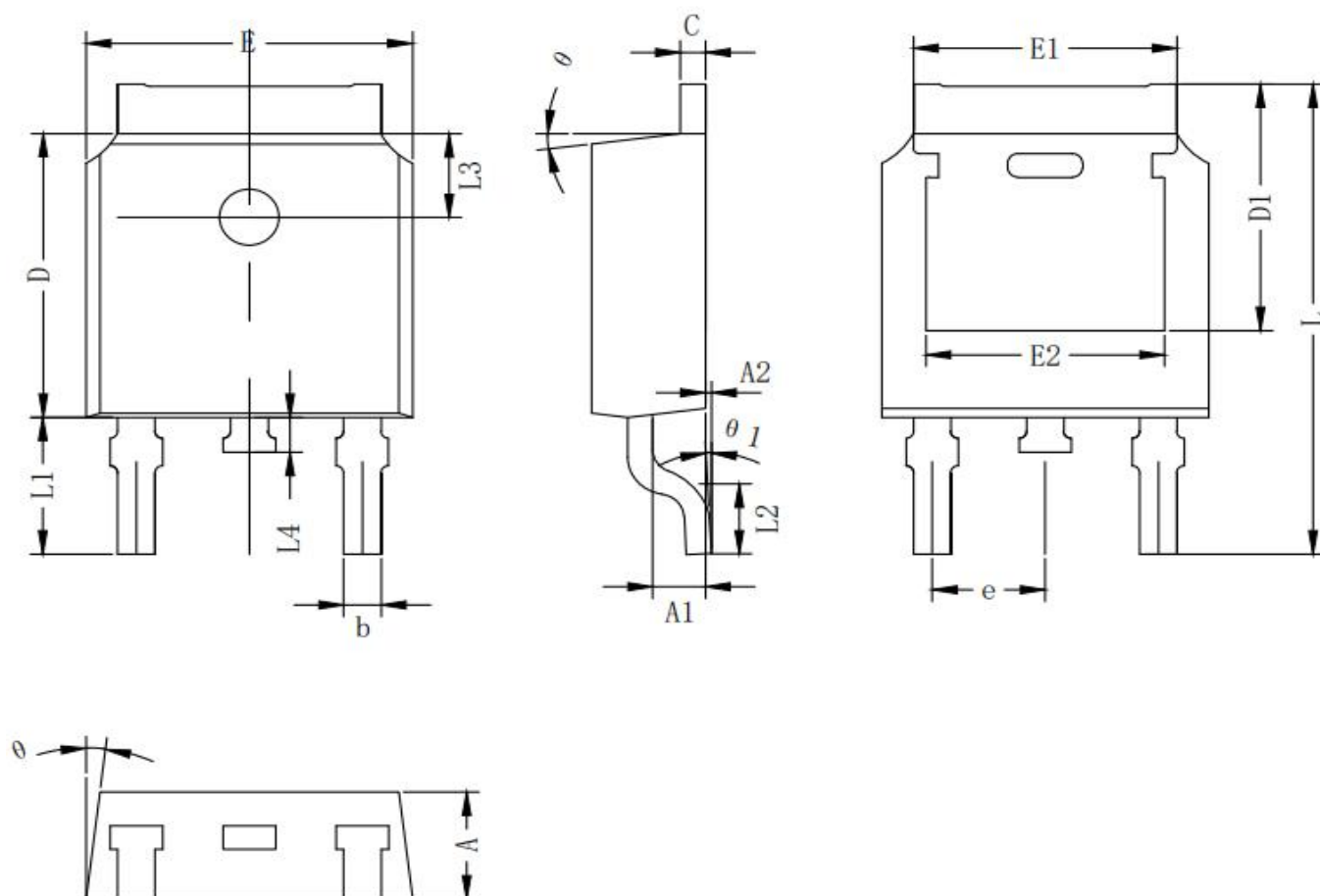


Figure 8 Transient Thermal Impedance

**Package outline drawing(TO-252 Unit: mm )**


符号	尺寸		符号	尺寸		符号	尺寸	
	Min	Max		Min	Max		Min	Max
A	2.10	2.50	D1	5.10	5.45	L2	1.4	1.7
A1	0.97	1.17	E	6.4	6.8	L3	1.65	1.95
A2	0.00	0.12	E1	5.1	5.45	L4	0.60	1.00
b	0.66	0.86	E2	4.63	5.03	e	2.286BSC	
C	0.45	0.6	L	9.90	10.30	0	5	10
D	5.90	6.30	L1	2.74	3.14	0 1	0	3

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